



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

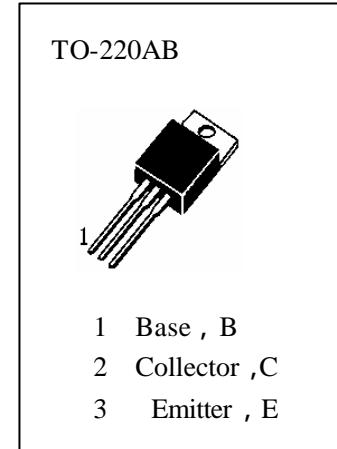
**HEP41C**

## APPLICATIONS

Medium Power Linear Switching Application.

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$	—Storage Temperature.....	-55~150
$T_j$	—Junction Temperature.....	150
$P_c$	—Collector Dissipation ( $T_c=25^\circ C$ ) .....	65W
$P_c$	—Collector Dissipation ( $T_A=25^\circ C$ ) .....	2W
$V_{CBO}$	—Collector-Base Voltage.....	100V
$V_{CEO}$	—Collector-Emitter Voltage.....	100V
$V_{EBO}$	—Emitter-Base Voltage.....	5V
$I_c$	—Collector Current.....	6A
$I_b$	—Base Current.....	2A



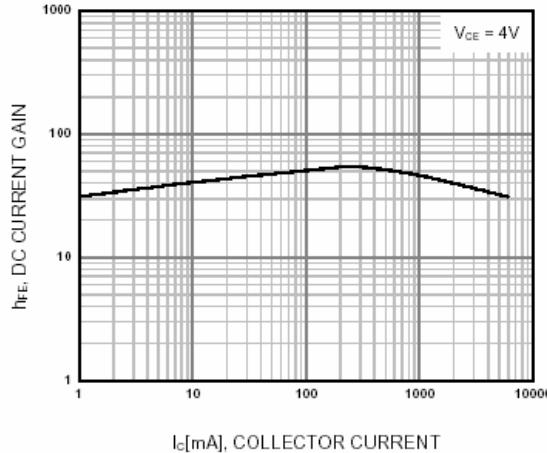
## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	100			V	$I_C=30mA, I_B=0$
$I_{CEO}$	Collector Cut-off Current			0.7	mA	$V_{CE}=60V, I_B=0$
$I_{EBO}$	Emitter Cut-off Current			1	mA	$V_{EB}=5V, I_C=0$
$I_{CES}$	Collector Cut-off Current			400	$\mu A$	$V_{CE}=100V, V_{EB}=0$
$HFE(1)$	DC Current Gain	30				$V_{CE}=4V, I_C=0.3A$
$HFE(2)$	DC Current Gain	15		75		$V_{CE}=4V, I_C=3A$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			1.5	V	$I_C=6A, I_B=600mA$
$V_{BE(on)}$	Base-Emitter On Voltage			2.0	V	$V_{CE}=4V, I_C=6A$
$f_T$	Current Gain-Bandwidth Product	3.0			MHz	$V_{CE}=10V, I_C=500mA, f=1MHz$

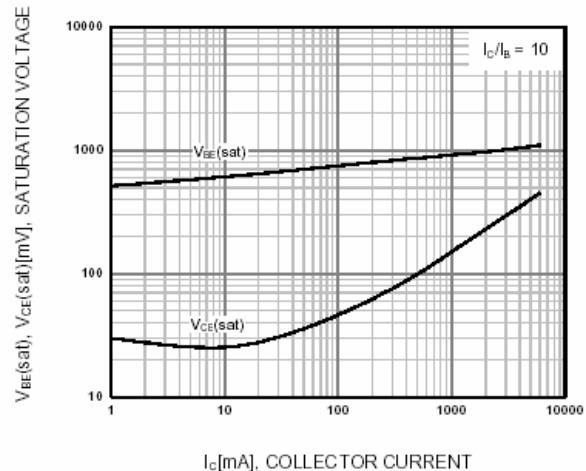


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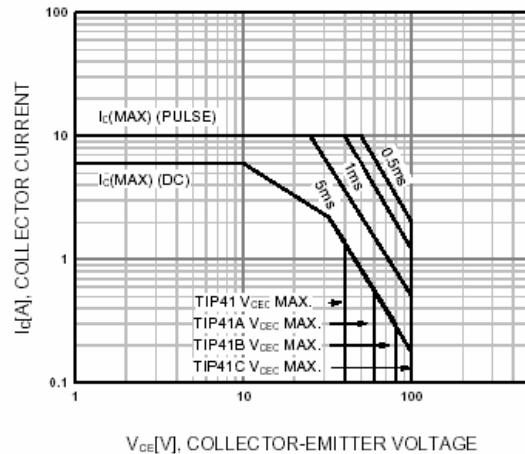
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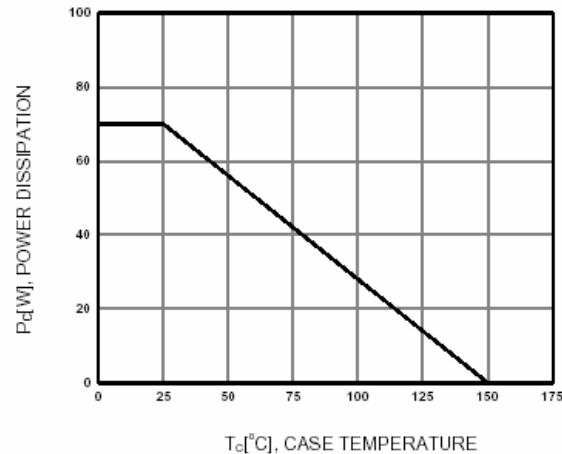
**Figure 1. DC current Gain**



**Figure 2. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage**



**Figure 3. Safe Operating Area**



**Figure 4. Power Derating**